

2SJ576

Silicon P Channel MOS FET
High Speed Switching

HITACHI

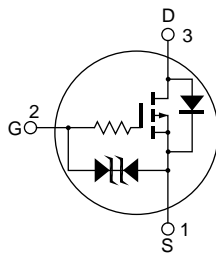
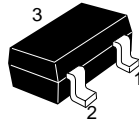
ADE-208-741B (Z)
3rd.Edition.
June 1999

Features

- Low on-resistance
 $R_{DS} = 2.8 \Omega$ typ. ($V_{GS} = -10 \text{ V}$, $I_D = -50 \text{ mA}$)
 $R_{DS} = 5.7 \Omega$ typ. ($V_{GS} = -4 \text{ V}$, $I_D = -50 \text{ mA}$)
- 4 V gate drive device.
- Small package (CMPAK)

Outline

CMPAK



1. Source
2. Gate
3. Drain

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-30	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	-100	mA
Drain peak current	$I_{D(pulse)}$ ^{Note 1}	-400	mA
Body-drain diode reverse drain current	I_{DR}	-100	mA
Channel dissipation	Pch ^{Note 2}	300	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

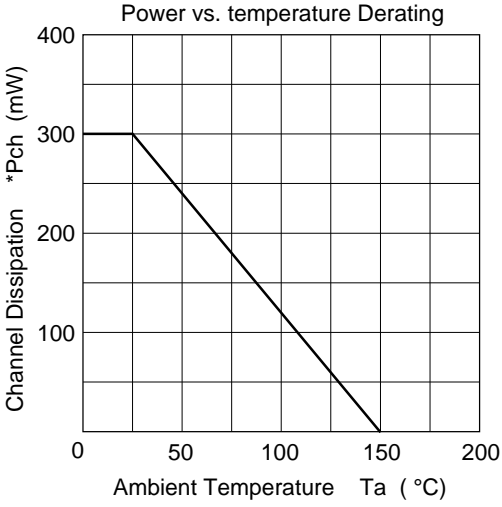
Note: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
 2. Value on the alumina ceramic board (12.5x20x0.7 mm)

Electrical Characteristics (Ta = 25°C)

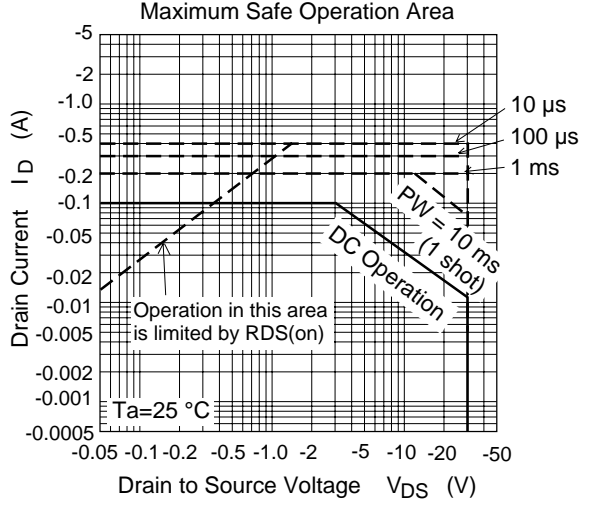
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -100 \mu A, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \mu A, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 5	μA	$V_{GS} = \pm 16 V, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-1	μA	$V_{DS} = -30 V, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.3	—	-2.3	V	$I_D = -10 \mu A, V_{DS} = -5 V$
Static drain to source on state resistance	$R_{DS(on)}$	—	2.8	3.3	Ω	$I_D = -50 mA, V_{GS} = -10 V$ ^{Note 3}
	$R_{DS(on)}$	—	5.7	7.9	Ω	$I_D = -50 mA, V_{GS} = -4 V$ ^{Note 3}
Forward transfer admittance	$ y_{fs} $	68	105	—	mS	$I_D = -50 mA, V_{DS} = -10 V$ ^{Note 3}
Input capacitance	Ciss	—	25	—	pF	$V_{DS} = -10 V$
Output capacitance	Coss	—	20	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	8	—	pF	$f = 1 MHz$
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$I_D = -50 mA, V_{GS} = -10 V$
Rise time	t_r	—	15	—	ns	$R_L = 200 \Omega$
Turn-off delay time	$t_{d(off)}$	—	40	—	ns	
Fall time	t_f	—	45	—	ns	

Note: 3. Pulse test
 4. Marking is AP
 See characteristics curves of 2SJ575

Main Characteristics



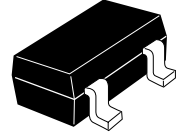
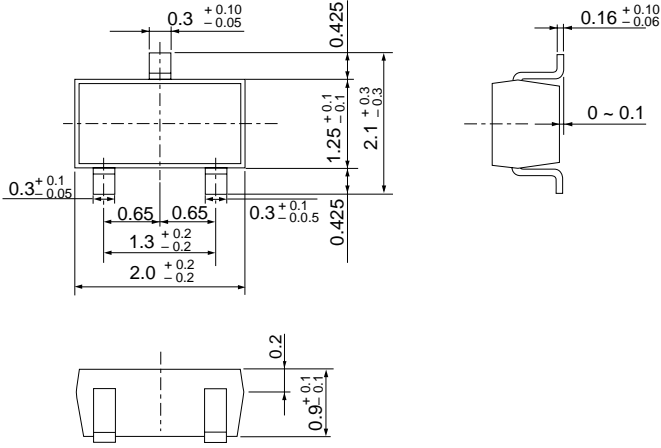
*Value on the alumina ceramic board.(12.5x20x0.7mm)



Value on the alumina ceramic board.(12.5x20x0.7mm)

Package Dimensions

Unit: mm



Hitachi Code	CMPAK
EIAJ	SC-70
JEDEC	-

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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